

## Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

[IXYS Corporation](#)

[IXTT500N04T2](#)

For any questions, you can email us directly:

[sales@integrated-circuit.com](mailto:sales@integrated-circuit.com)

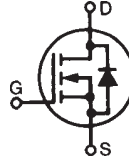
**TrenchT2™  
Power MOSFET**
**IXTH500N04T2  
IXTT500N04T2**

$$V_{DSS} = 40V$$

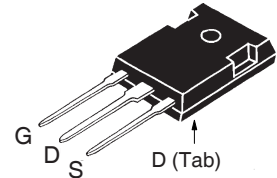
$$I_{D25} = 500A$$

$$R_{DS(on)} \leq 1.6m\Omega$$

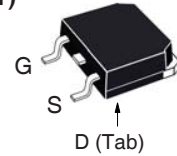
N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode



TO-247 (IXTH)



TO-268 (IXTT)



G = Gate      D = Drain  
S = Source    Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $175^\circ C$	40	V
$V_{DGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GS} = 1M\Omega$	40	V
$V_{GSM}$	Transient	$\pm 20$	V
$I_{D25}$	$T_C = 25^\circ C$ (Chip Capability)	500	A
$I_{LRMS}$	Lead Current Limit, RMS	160	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	1250	A
$I_A$	$T_C = 25^\circ C$	100	A
$E_{AS}$	$T_C = 25^\circ C$	800	mJ
$P_D$	$T_C = 25^\circ C$	1000	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	1.6mm (0.062in.) from Case for 10s	300	$^\circ C$
$T_{sold}$	Plastic Body for 10 seconds	260	$^\circ C$
$M_d$	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

**Features**

- International Standard Packages
- $175^\circ C$  Operating Temperature
- High Current Handling Capability
- Avalanche Rated
- Fast Intrinsic Diode
- Low  $R_{DS(on)}$

**Advantages**

- Easy to Mount
- Space Savings
- High Power Density

**Applications**

- Synchronous Buck Converters
- High Current Switching Power Supplies
- Battery Powered Electric Motors
- Resonant-Mode Power Supplies
- Electronics Ballast Application
- Class D Audio Amplifiers

Symbol	Test Conditions ( $T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	40		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	1.5		3.5 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 150^\circ C$			10 $\mu A$
				750 $\mu A$
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 100A$ , Notes 1 & 2			1.6 m $\Omega$



**IXTH500N04T2**  
**IXTT500N04T2**

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}, I_D = 60\text{A}$ , Note 1	75	125	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		25	nF
$C_{oss}$			4410	pF
$C_{rss}$			970	pF
$R_{Gi}$	Gate Input Resistance		1.1	$\Omega$
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 200\text{A}$ $R_G = 1\Omega$ (External)		37	ns
$t_r$			16	ns
$t_{d(off)}$			68	ns
$t_f$			44	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		405	nC
$Q_{gs}$			105	nC
$Q_{gd}$			118	nC
$R_{thJC}$	TO-247			0.15 $^\circ\text{C/W}$
$R_{thCH}$			0.21	$^\circ\text{C/W}$

**Source-Drain Diode**

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			500 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			1500 A
$V_{SD}$	$I_F = 100\text{A}, V_{GS} = 0\text{V}$ , Note 1			1.2 V
$t_{rr}$	$I_F = 100\text{A}, V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 20\text{V}$		84	ns
$I_{RM}$			3.1	A
$Q_{RM}$			130	nC

Notes:

1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Includes lead resistance.

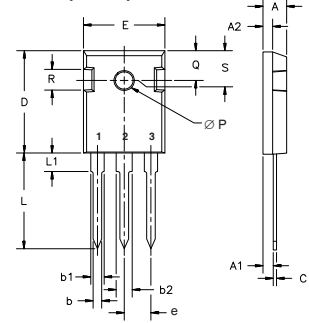
**ADVANCE TECHNICAL INFORMATION**

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338 B2  
4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

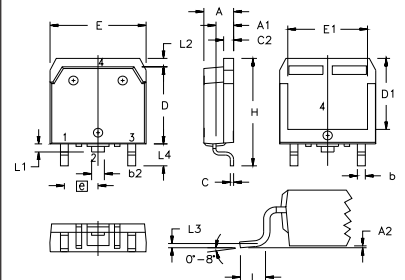
**TO-247 (IXTH) Outline**



Terminals: 1 - Gate  
2 - Drain  
3 - Source  
Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.087	.102
b <sub>1</sub>	1.0	1.4	.040	.055
b <sub>2</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L <sub>1</sub>		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

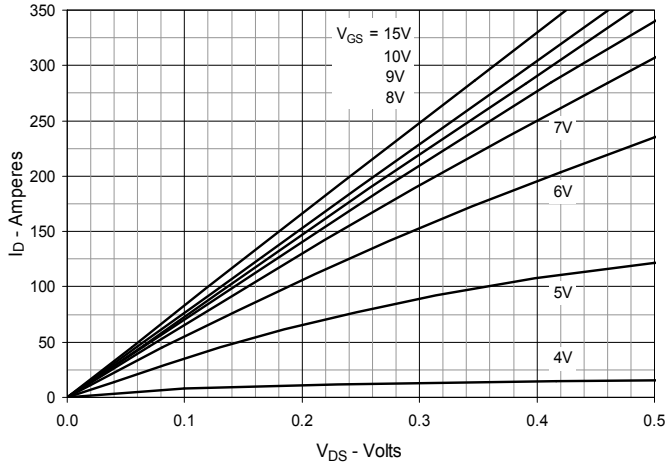
**TO-268 (IXTT) Outline**



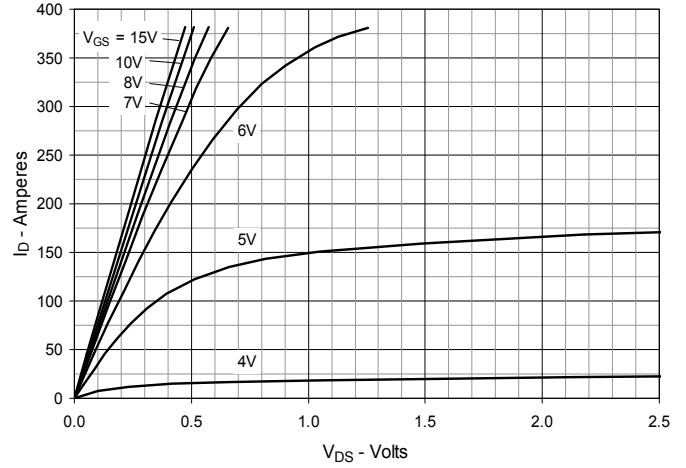
Terminals: 1 - Gate  
2 - Drain  
3 - Source  
Tab - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A <sub>1</sub>	.106	.114	2.70	2.90
A <sub>2</sub>	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b <sub>2</sub>	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C <sub>2</sub>	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D <sub>1</sub>	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E <sub>1</sub>	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L <sub>1</sub>	.047	.055	1.20	1.40
L <sub>2</sub>	.039	.045	1.00	1.15
L <sub>3</sub>	.010 BSC		0.25 BSC	
L <sub>4</sub>	.150	.161	3.80	4.10

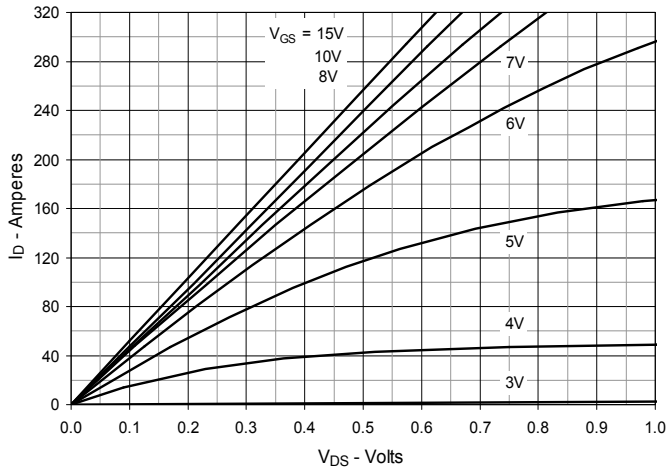
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



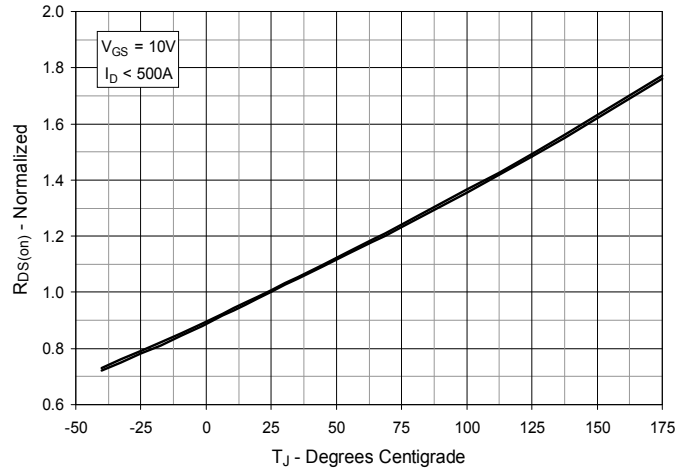
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



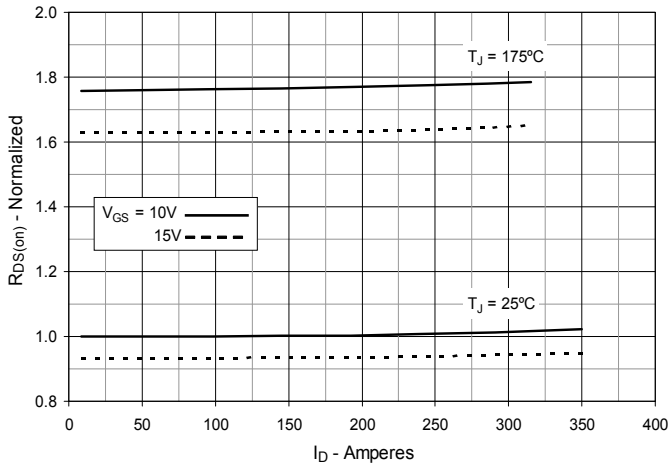
**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**



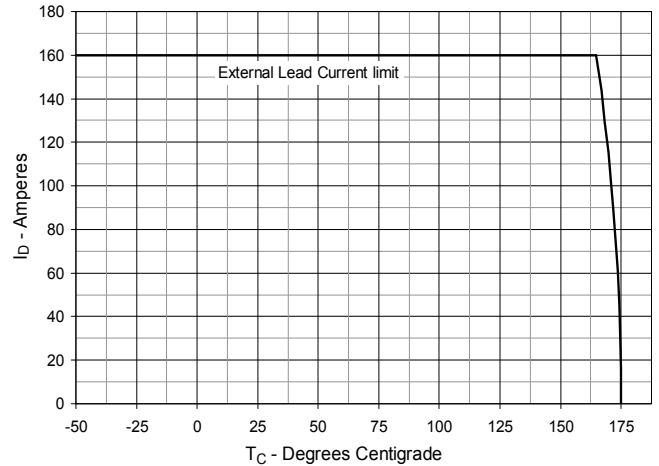
**Fig. 4.  $R_{DS(on)}$  Normalized vs. Junction Temperature**



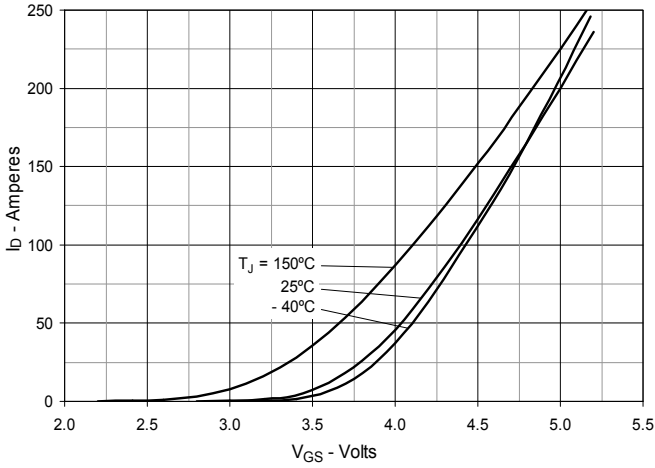
**Fig. 5.  $R_{DS(on)}$  Normalized vs. Drain Current**



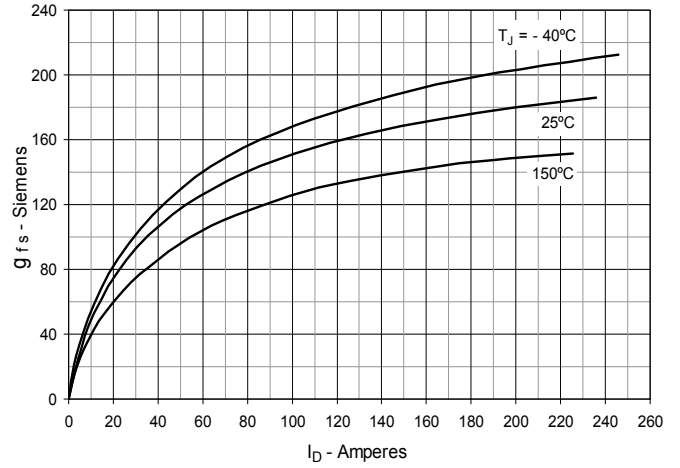
**Fig. 6. Drain Current vs. Case Temperature**



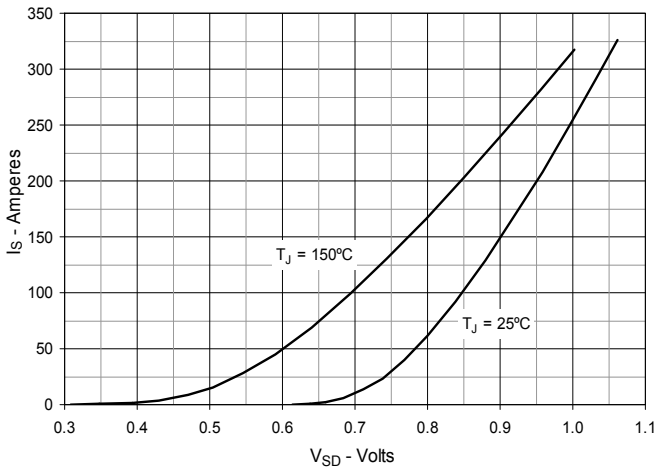
**Fig. 7. Input Admittance**



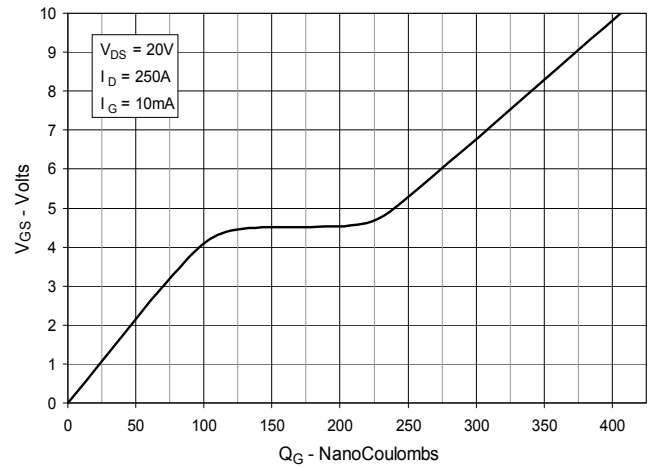
**Fig. 8. Transconductance**



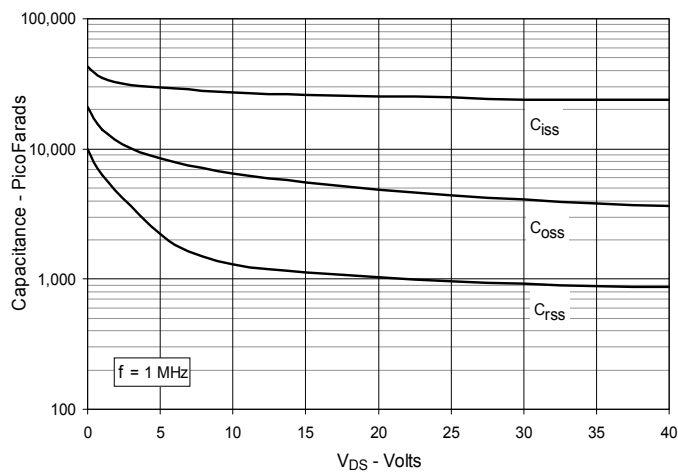
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



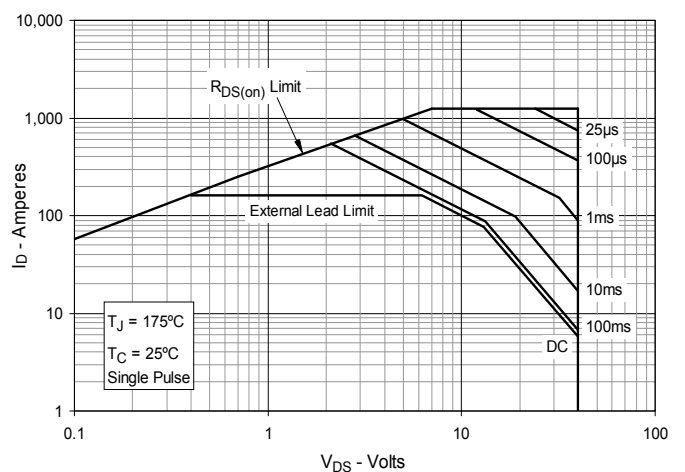
**Fig. 10. Gate Charge**



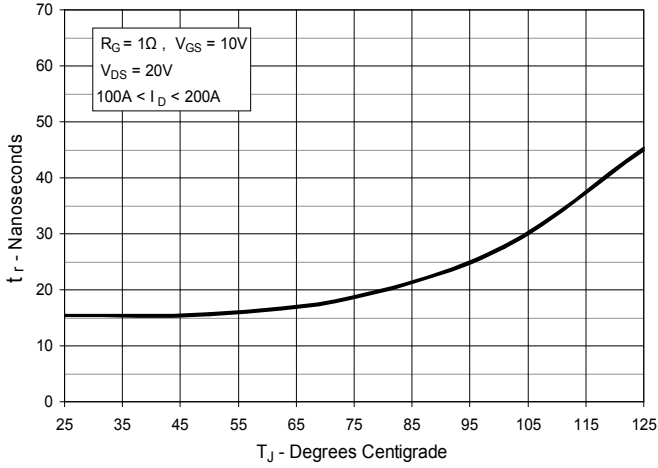
**Fig. 11. Capacitance**



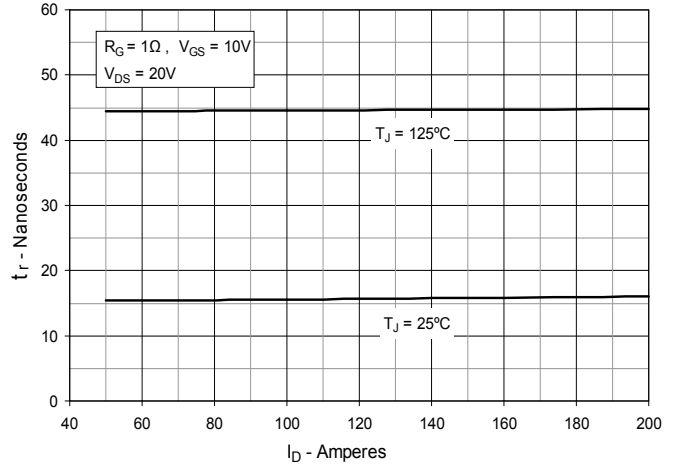
**Fig. 12. Forward-Bias Safe Operating Area**



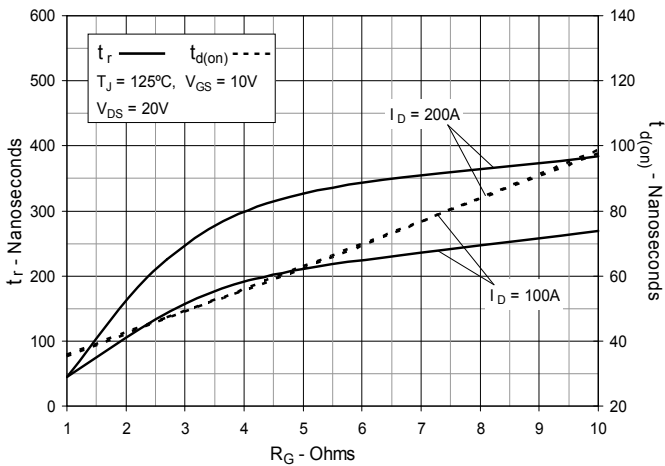
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



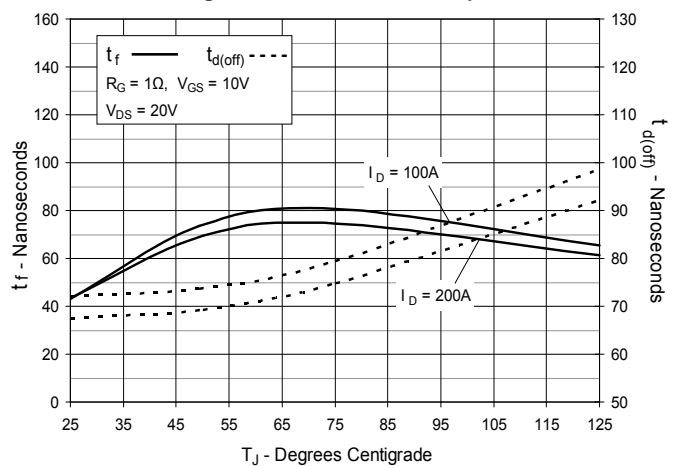
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



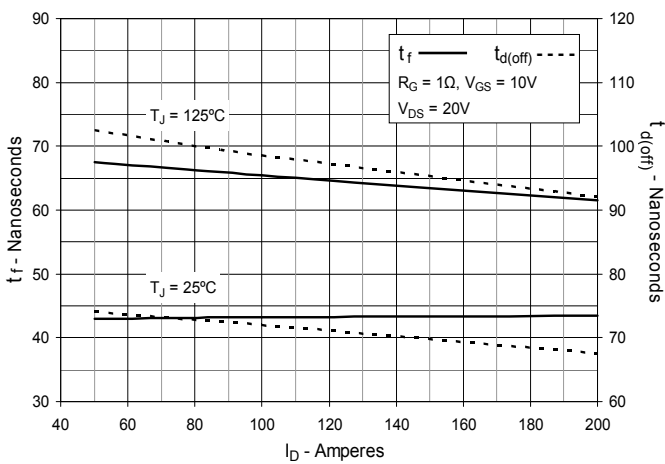
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**

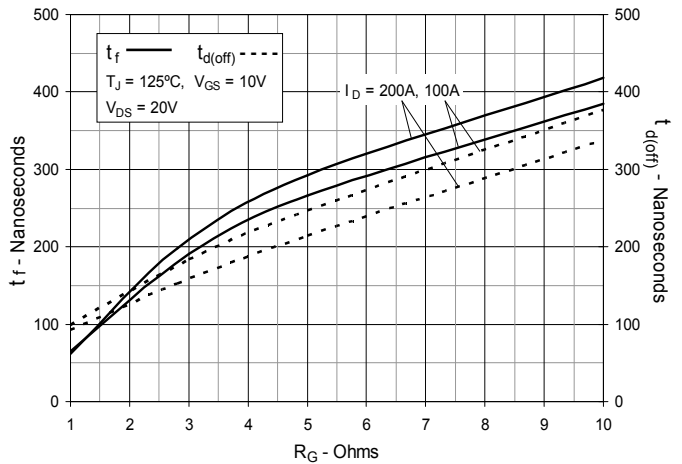


Fig. 19. Maximum Transient Thermal Impedance

